Yee-Chia Yeo

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

302	6,060	41	64
papers	citations	h-index	g-index

370	6,767	3.1	5.55
ext. papers	ext. citations	avg, IF	L-index

#	Paper	IF	Citations
302	A Ladder Transmission Line Model for the Extraction of Ultralow Specific Contact Resistivity—Part I: Theoretical Design and Simulation Study. *IEEE Transactions on Electron Devices*, **2020**, 67, 2682-2689	2.9	1
301	A Ladder Transmission Line Model for the Extraction of Ultralow Specific Contact Resistivity—Part II: Experimental Verification. *IEEE Transactions on Electron Devices*, **2020**, 67, 2690-2696	2.9	1
300	Design and Experimental Demonstration of Integrated Over-Current Protection Circuit for GaN DC–DC Converters. *IEEE Journal of Emerging and Selected Topics in Power Electronics*, **2020**, 8, 4270-4278	5.6	4
299	All-GaN Power Integration: Devices to Functional Subcircuits and Converter ICs. *IEEE Journal of Emerging and Selected Topics in Power Electronics*, **2020**, 8, 31-41	5.6	13
298	Elimination of the Parasitic Metal Resistance in Transmission Line Model for Extraction of Ultralow Specific Contact Resistivity. *IEEE Transactions on Electron Devices*, **2019**, 66, 3086-3092	2.9	7
297	Development of GaN Power IC Platform and All GaN DC-DC Buck Converter IC **2019**,		5
296	High-speed photo detection at two-micron-wavelength: technology enablement by GeSn/Ge multiple-quantum-well photodiode on 300 mm Si substrate. *Optics Express*, **2019**, 27, 5798-5813	3.3	48
295	Integrating GeSn photodiode on a 200 mm Ge-on-insulator photonics platform with Ge CMOS devices for advanced OEIC operating at 2 μm band. *Optics Express*, **2019**, 27, 26924-26939	3.3	18
294	Enhanced Photo Response at Two-micron-wavelength Using GeSn/Ge Multiple-Quantum-Well Waveguide **2019**,		1
293	Strain relaxation of germanium-tin (GeSn) fins. *AIP Advances*, **2018**, 8, 025111	1.5	5
292	Nanoscale metal-InGaAs contacts with ultra-low specific contact resistivity: Improved interfacial quality and extraction methodology. *Journal of Applied Physics*, **2018**, 123, 024508	2.5	10
291	High-performance GeSn photodetector and fin field-effect transistor (FinFET) on an advanced GeSn-on-insulator platform. *Optics Express*, **2018**, 26, 10305-10314	3.3	16
290	GeSn lateral p-i-n photodetector on insulating substrate. *Optics Express*, **2018**, 26, 17312-17321	3.3	25
289	Germanium-Tin (GeSn) P-Channel Fin Field-Effect Transistor Fabricated on a Novel GeSn-on-Insulator Substrate. *IEEE Transactions on Electron Devices*, **2018**, 65, 3754-3761	2.9	19
288	High Speed ($boldsymbol{f}_{3-boldsymbol{d}boldsymbol{B}}$ above 10 GHz) Photo Detection at Two-micron-wavelength Realized by GeSn/Ge Multiple-quantum-well Photodiode on a 300 mm Si Substrate **2018**,		1
287	Sub- $10^{-textsf{9}},,Omegacdot{text{cm}}^{textsf{2}}$ Specific Contact Resistivity (Down to $textsf{4.4}timestextsf{10}^{-textsf{10}},,Omegacdottextsf{cm}^{textsf{2}}$) for Metal Contact on Ga and Sn Surface-Segregated GeSn Film. *IEEE Transactions on Electron Devices*, **2018**, 65, 5275-5281	2.9	11
286	An Improved Methodology for Accurate Extraction of Ultra-Low Specific Contact Resistivity of Alloyed Contacts Using Nanoscale Transmission Line Method. *IEEE Electron Device Letters*, **2018**, 39, 803-806	4.4	5

285	Monolithic Integration of InAs Quantum-Well n-MOSFETs and Ultrathin Body Ge p-MOSFETs on a Si Substrate. *IEEE Transactions on Electron Devices*, **2017**, 64, 353-360	2.9	8
284	Nanoscale FETs Simulation Based on Full-Complex-Band Structure and Self-Consistently Solved Atomic Potential. *IEEE Transactions on Electron Devices*, **2017**, 64, 58-65	2.9	5
283	Enabling low power and high speed OEICs: First monolithic integration of InGaAs n-FETs and lasers on Si substrate **2017**,		1
282	Record low specific contact resistivity (1.2 109 cm2) for P-type semiconductors: Incorporation of Sn into Ge and in-Situ Ga doping **2017**,		2
281	Digital Etch Technique for Forming Ultra-Scaled Germanium-Tin (Ge Sn) Fin Structure. *Scientific Reports*, **2017**, 7, 1835	4.9	10
280	The first GeSn FinFET on a novel GeSnOI substrate achieving lowest S of 79 mV/decade and record high Gm, int of 807 S/m for GeSn P-FETs **2017**,		15
279	Ultra-low specific contact resistivity (1.4 109 cm2) for metal contacts on in-situ Ga-doped Ge0.95Sn0.05 film. *Journal of Applied Physics*, **2017**, 122, 224503	2.5	19
278	Kinetics of plasma oxidation of germanium-tin (GeSn). *Applied Surface Science*, **2017**, 425, 95-99	6.7	1
277	Au-Free AlGaN/GaN MIS-HEMTs With Embedded Current Sensing Structure for Power Switching Applications. *IEEE Transactions on Electron Devices*, **2017**, 64, 3515-3518	2.9	14
276	Design of power integrated circuits in full AlGaN/GaN MIS-HEMT configuration for power conversion. *Physica Status Solidi (A) Applications and Materials Science*, **2017**, 214, 1600562	1.6	9
275	Thermal stability of germanium-tin (GeSn) fins. *Applied Physics Letters*, **2017**, 111, 252103	3.4	6
274	Two-micron-wavelength germanium-tin photodiodes with low dark current and gigahertz bandwidth. *Optics Express*, **2017**, 25, 15818-15827	3.3	60
273	Floating-base germanium-tin heterojunction phototransistor for high-efficiency photodetection in short-wave infrared range. *Optics Express*, **2017**, 25, 18502-18507	3.3	38
272	Germanium-tin multiple quantum well on silicon avalanche photodiode for photodetection at two micron wavelength. *Semiconductor Science and Technology*, **2016**, 31, 095001	1.8	21
271	Germanium-Tin heterojunction phototransistor: Towards high-efficiency low-power photodetection in short-wave infrared range **2016**,		3
270	Heteroepitaxial growth of In0.30Ga0.70As high-electron mobility transistor on 200 mm silicon substrate using metamorphic graded buffer. *AIP Advances*, **2016**, 6, 085106	1.5	9
269	Realistic Trap Configuration Scheme With Fabrication Processes in Consideration for the Simulations of AlGaN/GaN MIS-HEMT Devices. *IEEE Journal of Emerging and Selected Topics in Power Electronics*, **2016**, 4, 720-729	5.6	8
268	Single Crystalline Germanium-Lead Formed by Laser-Induced Epitaxy. *ECS Journal of Solid State Science and Technology*, **2016**, 5, P353-P360	2	6

267	Gate-All-Around In0.53Ga0.47As Junctionless Nanowire FET With Tapered Source/Drain Structure. *IEEE Transactions on Electron Devices*, **2016**, 63, 1027-1033	2.9	9
266	Ultimate Performance Projection of Ultrathin Body Transistor Based on Group IV, III-V, and 2-D-Materials. *IEEE Transactions on Electron Devices*, **2016**, 63, 773-780	2.9	13
265	Growth and characterization of highly tensile strained Ge1−xSnx formed on relaxed InyGa1−yP buffer layers. *Journal of Applied Physics*, **2016**, 119, 125303	2.5	3
264	Germanium–tin interdiffusion in strained Ge/GeSn multiple-quantum-well structure. *Journal Physics D: Applied Physics*, **2016**, 49, 225102	3	6
263	Near-bandgap optical properties of pseudomorphic GeSn alloys grown by molecular beam epitaxy. *Journal of Applied Physics*, **2016**, 120, 063104	2.5	8
262	GeSn-on-insulator substrate formed by direct wafer bonding. *Applied Physics Letters*, **2016**, 109, 022106	3.4	25
261	Ge0.83Sn0.17 p-channel metal-oxide-semiconductor field-effect transistors: Impact of sulfur passivation on gate stack quality. *Journal of Applied Physics*, **2016**, 119, 024502	2.5	29
260	In-situ gallium-doping for forming p+ germanium-tin and application in germanium-tin p-i-n photodetector. *Journal of Applied Physics*, **2016**, 119, 155704	2.5	24
259	Effect of Body Thickness on the Electrical Performance of Ballistic n-Channel GaSb Double-Gate Ultrathin-Body Transistor. *IEEE Transactions on Electron Devices*, **2015**, 62, 788-794	2.9	8
258	Suppression of dark current in germanium-tin on silicon p-i-n photodiode by a silicon surface passivation technique. *Optics Express*, **2015**, 23, 18611-9	3.3	46
257	Germanium n-Channel Planar FET and FinFET: Gate-Stack and Contact Optimization. *IEEE Transactions on Electron Devices*, **2015**, 62, 3567-3574	2.9	12
256	Probing the carrier concentration profiles in phosphorus-implanted germanium using infrared spectroscopic ellipsometry. *Journal of Applied Physics*, **2015**, 117, 073103	2.5	
255	Influence of hydrogen surface passivation on Sn segregation, aggregation, and distribution in GeSn/Ge(001) materials. *Journal of Applied Physics*, **2015**, 117, 205302	2.5	10
254	Self-assembly of tin wires via phase transformation of heteroepitaxial germanium-tin on germanium substrate. *Journal of Applied Physics*, **2015**, 117, 225304	2.5	13
253	Critical thickness for strain relaxation of Ge1−xSnx (x≤0.17) grown by molecular beam epitaxy on Ge(001). *Applied Physics Letters*, **2015**, 106, 232106	3.4	54
252	Mid-infrared to ultraviolet optical properties of InSb grown on GaAs by molecular beam epitaxy. *Journal of Applied Physics*, **2015**, 117, 223106	2.5	4
251	Germanium-Tin on Si Avalanche Photodiode: Device Design and Technology Demonstration. *IEEE Transactions on Electron Devices*, **2015**, 62, 128-135	2.9	42
250	Avalanche photodiode featuring Germanium-tin multiple quantum wells on silicon: Extending photodetection to wavelengths of 2 and beyond **2015**,		3

249	Post-growth annealing of germanium-tin alloys using pulsed excimer laser. *Journal of Applied Physics*, **2015**, 118, 025701	2.5	8
248	Etching of germanium-tin using ammonia peroxide mixture. *Journal of Applied Physics*, **2015**, 118, 245303	2.5	4
247	Parametrized dielectric functions of amorphous GeSn alloys. *Journal of Applied Physics*, **2015**, 118, 123102	2.5	1
246	Germanium-based transistors for future high performance and low power logic applications **2015**,		17
245	An Expandable ${rm ZnS}hbox{-}{rm SiO}_{2}$ Liner Stressor for N-Channel FinFETs. *IEEE Transactions on Electron Devices*, **2014**, 61, 1963-1971	2.9	
244	Ballistic Transport Performance of Silicane and Germanane Transistors. *IEEE Transactions on Electron Devices*, **2014**, 61, 1590-1598	2.9	44
243	Migration enhanced epitaxy of InGaP on offcut Ge (001) using solid-source molecular beam epitaxy **2014**,		1
242	Plasma Doping of InGaAs at Elevated Substrate Temperature for Reduced Sheet Resistance and Defect Formation. *IEEE Transactions on Electron Devices*, **2014**, 61, 3159-3165	2.9	1
241	Tin surface segregation, desorption, and island formation during post-growth annealing of strained epitaxial Ge1�Snx layer on Ge(001) substrate. *Applied Surface Science*, **2014**, 321, 240-244	6.7	39
240	Toward Conformal Damage-Free Doping With Abrupt Ultrashallow Junction: Formation of Si Monolayers and Laser Anneal as a Novel Doping Technique for InGaAs nMOSFETs. *IEEE Transactions on Electron Devices*, **2014**, 61, 1039-1046	2.9	26
239	GeTe Liner Stressor Featuring Phase-Change- Induced Volume Contraction for Strain Engineering of Sub-50-nm p-Channel FinFETs: Simulation and Electrical Characterization. *IEEE Transactions on Electron Devices*, **2014**, 61, 2647-2655	2.9	1
238	P2S5/(NH4)2Sx-Based Sulfur Monolayer Doping for Source/Drain Extensions in n-Channel InGaAs FETs. *IEEE Transactions on Electron Devices*, **2014**, 61, 2767-2773	2.9	4
237	Compositional dependence of optical critical point parameters in pseudomorphic GeSn alloys. *Journal of Applied Physics*, **2014**, 116, 053520	2.5	23
236	Above-bandgap optical properties of biaxially strained GeSn alloys grown by molecular beam epitaxy. *Applied Physics Letters*, **2014**, 104, 022111	3.4	31
235	InAlP-Capped (100) Ge nFETs with 1.06 nm EOT: Achieving record high peak mobility and first integration on 300 mm Si substrate **2014**,		1
234	Chlorine- and Fluorine-based dry etching of Germanium-Tin **2014**,		1
233	Formation of vertically stacked germanium-tin (Ge1�Snx) nanowires using a selective dry etch technique **2014**,		2
232	Cold Silicon Preamorphization Implant and Presilicide Sulfur Implant for Advanced Nickel Silicide Contacts. *IEEE Transactions on Electron Devices*, **2014**, 61, 3499-3506	2.9	2

231	Towards simultaneous achievement of carrier activation and crystallinity in Ge and GeSn with heated phosphorus ion implantation: An optical study. *Applied Physics Letters*, **2014**, 105, 122108	3.4	11
230	Infrared spectroscopic ellipsometry study of sulfur-doped In0.53Ga0.47As ultra-shallow junctions. *Applied Physics Letters*, **2014**, 104, 232102	3.4	4
229	Band alignment of HfO2/Al0.25Ga0.75N determined by x-ray photoelectron spectroscopy: Effect of SiH4 surface treatment. *Applied Physics Letters*, **2014**, 104, 091605	3.4	12
228	Self-Aligned and Non-Self-Aligned Contact Metallization in InGaAs Metal-Oxide-Semiconductor Field-Effect Transistors: A Simulation Study. *IEEE Transactions on Electron Devices*, **2014**, 61, 734-741	2.9	3
227	Silicon Surface Passivation Technology for Germanium-Tin P-Channel MOSFETs: Suppression of Germanium and Tin Segregation for Mobility Enhancement. *ECS Journal of Solid State Science and Technology*, **2014**, 3, Q162-Q168	2	11
226	New materials for post-Si computing: Ge and GeSn devices. *MRS Bulletin*, **2014**, 39, 678-686	3.2	42
225	Investigation of Pd-InGaAs for the formation of self-aligned source/drain contacts in InGaAs metal-oxide-semiconductor field-effect transistors. *Solid-State Electronics*, **2013**, 85, 36-42	1.7	8
224	Strained germanium-tin (GeSn) p-channel metal-oxide-semiconductor field-effect-transistors (p-MOSFETs) with ammonium sulfide passivation. *Solid-State Electronics*, **2013**, 83, 66-70	1.7	26
223	High performance Ge CMOS with novel InAlP-passivated channels for future sub-10 nm technology node applications **2013**,		9
222	Phase Change Liner Stressor for Strain Engineering of P-Channel FinFETs. *IEEE Transactions on Electron Devices*, **2013**, 60, 2703-2711	2.9	2
221	Near ballistic sub-7 nm Junctionless FET featuring 1 nm extremely-thin channel and raised S/D structure **2013**,		6
220	Novel technique comprising silane treatment and laser anneal for abrupt ultra-shallow junction formation for InGaAs n-MOSFETs **2013**,		3
219	Lattice strain analysis of silicon fin field-effect transistor structures wrapped by Ge2Sb2Te5 liner stressor. *Journal of Applied Physics*, **2013**, 113, 073708	2.5	7
218	Ultimate performance projection of ballistic III-V ultra-thin-body MOSFET **2013**,		1
217	Germanium-Tin (GeSn) p-Channel MOSFETs Fabricated on (100) and (111) Surface Orientations With Sub-400 $^{circ}hbox{C} hbox{Si}_{2}hbox{H}_{6}$ Passivation. *IEEE Electron Device Letters*, **2013**, 34, 339-341	4.4	87
216	Technology options for reducing contact resistances in nanoscale metal-oxide-semiconductor field-effect transistors **2013**,		2
215	In0.53Ga0.47As FinFETs with self-aligned molybdenum contacts and HfO2/Al2O3 gate dielectric. *Solid-State Electronics*, **2013**, 84, 83-89	1.7	7
214	Contact Resistance Reduction for Strained N-MOSFETs With Silicon-Carbon Source/Drain Utilizing Aluminum Ion Implant and Aluminum Profile Engineering. *IEEE Transactions on Electron Devices*, **2013**, 60, 1310-1317	2.9	15

213	Sub-400 °C Si2H6 Passivation, HfO2 Gate Dielectric, and Single TaN Metal Gate: A Common Gate Stack Technology for In0.7Ga0.3As and Ge1-xSnx CMOS. *IEEE Transactions on Electron Devices*, **2013** , 60, 1640-1648	2.9	23
212	Germanium Multiple-Gate Field-Effect Transistor With In Situ Boron-Doped Raised Source/Drain. *IEEE Transactions on Electron Devices*, **2013**, 60, 2135-2141	2.9	7
211	Strain engineering of ultra-thin silicon-on-insulator structures using through-buried-oxide ion implantation and crystallization. *Solid-State Electronics*, **2013**, 83, 37-41	1.7	3
210	$hbox{Ni}(hbox{Ge}_{1 - x}hbox{Sn}_{x})$ Ohmic Contact Formation on N-Type $hbox{Ge}_{1 - x}hbox{Sn}_{x}$ Using Selenium or Sulfur Implant and Segregation. *IEEE Transactions on Electron Devices*, **2013**, 60, 746-752	2.9	20
209	Relaxed and Strained Patterned Germanium-Tin Structures: A Raman Scattering Study. *ECS Journal of Solid State Science and Technology*, **2013**, 2, P138-P145	2	51
208	Crystal structure and epitaxial relationship of Ni4InGaAs2 films formed on InGaAs by annealing. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2013**, 31, 012202	1.3	18
207	Germanium-tin n-channel tunneling field-effect transistor: Device physics and simulation study. *Journal of Applied Physics*, **2013**, 113, 194507	2.5	39
206	Tunneling field-effect transistor with Ge/In0.53Ga0.47As heterostructure as tunneling junction. *Journal of Applied Physics*, **2013**, 113, 094502	2.5	22
205	(110)-oriented germanium-tin (Ge0.97Sn0.03) P-channel MOSFETs **2013**,		2
204	Physical model for gallium arsenide growth on germanium fins with different orientations formed on 10° offcut germanium-on-insulator substrate. *Journal of Applied Physics*, **2013**, 113, 044301	2.5	
203	Germanium–Tin P-Channel Tunneling Field-Effect Transistor: Device Design and Technology Demonstration. *IEEE Transactions on Electron Devices*, **2013**, 60, 4048-4056	2.9	47
202	Gate Stack Reliability of MOSFETs With High-Mobility Channel Materials: Bias Temperature Instability. *IEEE Transactions on Device and Materials Reliability*, **2013**, 13, 524-533	1.6	16
201	Band alignment study of lattice-matched InAlP and Ge using x-ray photoelectron spectroscopy. *Applied Physics Letters*, **2013**, 103, 031604	3.4	8
200	Ge0.97Sn0.03 p-channel metal-oxide-semiconductor field-effect transistors: Impact of Si surface passivation layer thickness and post metal annealing. *Journal of Applied Physics*, **2013**, 114, 044510	2.5	38
199	Asymetrically strained high performance Germanium gate-all-around nanowire p-FETs featuring 3.5 nm wire width and contractible phase change liner stressor (Ge2Sb2Te5) **2013**,		2
198	Dopant Segregation and Nickel Stanogermanide Contact Formation on $hbox{p}^{+} hbox{Ge}_{0.947}hbox{Sn}_{0.053}$ Source/Drain. *IEEE Electron Device Letters*, **2012**, 33, 634-636	4.4	31
197	Contact Technology for Strained nFinFETs With Silicon–Carbon Source/Drain Stressors Featuring Sulfur Implant and Segregation. *IEEE Transactions on Electron Devices*, **2012**, 59, 1046-1055	2.9	12
196	A Self-Aligned Ni-InGaAs Contact Technology for InGaAs Channel n-MOSFETs. *Journal of the Electrochemical Society*, **2012**, 159, H511-H515	3.9	27

195	Selenium Segregation for Effective Schottky Barrier Height Reduction in NiGe/n�Ge Contacts. *IEEE Electron Device Letters*, **2012**, 33, 773-775	4.4	33
194	(NH4)2S Passivation for High Mobility Germanium-Tin (GeSn) p-MOSFETs **2012**,		1
193	High performance �gate Ge FinFET featuring low temperature Si2H6 passivation and implantless Schottky-barrier NiGe metallic Source/Drain **2012**,		2
192	Germanium�Tin $hbox{n}^{+}hbox{/p}$ Junction Formed Using Phosphorus Ion Implant and 400 $^{circ} hbox{C}$ Rapid Thermal Anneal. *IEEE Electron Device Letters*, **2012**, 33, 1529-1531	4.4	14
191	Towards direct band-to-band tunneling in P-channel tunneling field effect transistor (TFET): Technology enablement by Germanium-tin (GeSn) **2012**,		33
190	Metal stanogermanide contacts with enhanced thermal stability for high mobility germanium-tin field-effect transistor **2012**,		1
189	PBTI characteristics of N-channel tunneling field effect transistor with HfO2 gate dielectric: New insights and physical model **2012**,		1
188	CoInGaAs as a novel self-aligned metallic source/drain material for implant-less In0.53Ga0.47As n-MOSFETs. *Solid-State Electronics*, **2012**, 78, 62-67	1.7	9
187	Study of interfaces between phase-change material Ge2Sb2Te5 and prevalent complementary metal-oxide semiconductor materials by XPS. *Surface and Interface Analysis*, **2012**, 44, 1013-1017	1.5	4
186	Simulation of tunneling field-effect transistors with extended source structures. *Journal of Applied Physics*, **2012**, 111, 114514	2.5	13
185	Silicon-Carbon Source and Drain Stressors: Carbon Profile Design by Ion Implantation. *Journal of the Electrochemical Society*, **2012**, 159, H425-H432	3.9	1
184	In$_{0.53}$Ga$_{0.47}$As N-Channel Metal�Oxide�Semiconductor Field-Effect Transistors with Shallow Metallic Source and Drain Extensions and Offset N^{+} Doped Regions for Leakage Suppression. *Japanese Journal of Applied Physics*, **2012**, 51, 02BF03	1.4	2
183	Device Physics and Design of a L-Shaped Germanium Source Tunneling Transistor. *Japanese Journal of Applied Physics*, **2012**, 51, 02BC04	1.4	10
182	Ge/Ni�InGaAs Solid-State Reaction for Contact Resistance Reduction on n^{+} In$_{0.53}$Ga$_{0.47}$As. *Japanese Journal of Applied Physics*, **2012**, 51, 02BF06	1.4	2
181	Electronic band structure and effective mass parameters of Ge1-xSnx alloys. *Journal of Applied Physics*, **2012**, 112, 103715	2.5	159
180	Modulation of effective Schottky barrier height of nickel silicide on silicon using pre-silicide ammonium sulfide treatment. *Journal of Applied Physics*, **2012**, 111, 073705	2.5	10
179	Fermi-level depinning at the metal-germanium interface by the formation of epitaxial nickel digermanide NiGe2 using pulsed laser anneal. *Applied Physics Letters*, **2012**, 101, 172103	3.4	13
178	High-Performance Germanium $Omega$ -Gate MuGFET With Schottky-Barrier Nickel Germanide Source/Drain and Low-Temperature Disilane-Passivated Gate Stack. *IEEE Electron Device Letters*, **2012**, 33, 1336-1338	4.4	19

No.	Publication	IF	Citations
177	**2012**,		21
176	A new liner stressor (GeTe) featuring stress enhancement due to very large phase-change induced volume contraction for p-channel FinFETs **2012**,		2
175	Phase-Change Random Access Memory With Multilevel Resistances Implemented Using a Dual Phase-Change Material Stack. *IEEE Transactions on Electron Devices*, **2012**, 59, 2910-2916	2.9	6
174	Multiple-Gate In0.53Ga0.47As Channel n-MOSFETs with Self-Aligned Ni-InGaAs Contacts. *ECS Journal of Solid State Science and Technology*, **2012**, 1, P82-P85	2	16
173	Device Physics and Design of a L-Shaped Germanium Source Tunneling Transistor. *Japanese Journal of Applied Physics*, **2012**, 51, 02BC04	1.4	8
172	Ge/Ni–InGaAs Solid-State Reaction for Contact Resistance Reduction on n+In0.53Ga0.47As. *Japanese Journal of Applied Physics*, **2012**, 51, 02BF06	1.4	1
171	Bias temperature instability (BTI) characteristics of graphene Field-Effect Transistors **2011**,		6
170	Silicon-based tunneling field-effect transistor with elevated germanium source formed on (110) silicon substrate. *Applied Physics Letters*, **2011**, 98, 153502	3.4	48
169	Modeling the Negative Quadratic VCC of $hbox{SiO}_{2}$ in MIM Capacitor. *IEEE Electron Device Letters*, **2011**, 32, 1671-1673	4.4	10
168	Contact-Resistance Reduction for Strained n-FinFETs With Silicon–Carbon Source/Drain and Platinum-Based Silicide Contacts Featuring Tellurium Implantation and Segregation. *IEEE Transactions on Electron Devices*, **2011**, 58, 3852-3862	2.9	14
167	In0.7Ga0.3As channel n-MOSFETs with a novel self-aligned Ni-InGaAs contact formed using a salicide-like metallization process **2011**,		1
166	Impact of a Germanium and Carbon Preamorphization Implant on the Electrical Characteristics of NiSi/Si Contacts With a Presilicide Sulfur Implant. *IEEE Electron Device Letters*, **2011**, 32, 1734-1736	4.4	5
165	High-mobility germanium-tin (GeSn) P-channel MOSFETs featuring metallic source/drain and sub-370 °C process modules **2011**,		27
164	Pd-InGaAs as a new self-aligned contact material on InGaAs **2011**,		1
163	Self-aligned contact metallization technology for III-V metal-oxide-semiconductor field effect transistors. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2011**, 29, 032209	1.3	9
162	New Tellurium implant and segregation for contact resistance reduction and single metallic silicide technology for independent contact resistance optimization in n- and p-FinFETs **2011**,		1
161	Source/Drain Engineering for In0.7Ga0.3As N-Channel Metal–Oxide–Semiconductor Field-Effect Transistors: Raised Source/Drain withIn situDoping for Series Resistance Reduction. *Japanese Journal of Applied Physics*, **2011**, 50, 04DF01	1.4	6
160	III–V Multiple-Gate Field-Effect Transistors With High-Mobility $hbox{In}_{0.7}hbox{Ga}_{0.3}hbox{As}$ Channel and Epi-Controlled Retrograde-Doped Fin. *IEEE Electron Device Letters*, **2011**, 32, 146-148	4.4	55

159	Electrostatics of Ultimately Thin-Body Tunneling FET Using Graphene Nanoribbon. *IEEE Electron Device Letters*, **2011**, 32, 431-433	4.4	7
158	A new robust non-local algorithm for band-to-band tunneling simulation and its application to Tunnel-FET. *Solid-State Electronics*, **2011**, 57, 23-30	1.7	31
157	Source Engineering for Tunnel Field-Effect Transistor: Elevated Source with Vertical Silicon�Germanium/Germanium Heterostructure. *Japanese Journal of Applied Physics*, **2011**, 50, 04DJ07	1.4	12
156	Local stress induced by diamond-like carbon liner in AlGaN/GaN metal-oxide-semiconductor high-electron mobility transistors and impact on electrical characteristics. *Applied Physics Letters*, **2011**, 98, 183502	3.4	10
155	Photoelectron spectroscopy study of band alignment at interface between Ni-InGaAs and In0.53Ga0.47As. *Applied Physics Letters*, **2011**, 99, 012105	3.4	14
154	Schottky barrier height tuning of silicides on p-type Si (100) by aluminum implantation and pulsed excimer laser anneal. *Journal of Applied Physics*, **2011**, 110, 073703	2.5	8
153	Band offsets between SiO2 and phase change materials in the (GeTe)x(Sb2Te3)1� pseudobinary system. *Applied Physics Letters*, **2011**, 98, 132103	3.4	3
152	Novel technique to engineer aluminum profile at nickel-silicide/Silicon:Carbon interface for contact resistance reduction, and integration in strained N-MOSFETs with silicon-carbon stressors **2011**,		3
151	Self-Aligned Gate-First In[sub 0.7]Ga[sub 0.3]As n-MOSFETs with an InP Capping Layer for Performance Enhancement. *Electrochemical and Solid-State Letters*, **2011**, 14, H117		15
150	In[sub 0.7]Ga[sub 0.3]As Channel n-MOSFET with Self-Aligned Ni�InGaAs Source and Drain. *Electrochemical and Solid-State Letters*, **2011**, 14, H60		34
149	Source/Drain Engineering for In0.7Ga0.3As N-Channel Metal�Oxide�Semiconductor Field-Effect Transistors: Raised Source/Drain withIn situDoping for Series Resistance Reduction. *Japanese Journal of Applied Physics*, **2011**, 50, 04DF01	1.4	2
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1	Effects of high-/spl kappa/ dielectrics on the workfunctions of metal and silicon gates		1